NSN 5962-01-174-3361

Memory Microcircuit - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5962-01-174-3361

Body Length:

0.840 inches

Body Width:

Between 0.220 inches and 0.310 inches

Body Height:

Between 0.140 inches and 0.185 inches

Maximum Power Dissipation Rating:

739.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and positive outputs and schottky and programmable and programmed and bipolar and w/enable and w/decoded output and w/buffered output

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Case Outline Source And Designator:

D-2 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

75.00 nanoseconds propagation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

16 printed circuit

Specification Data:

81349-mil-m-38510/20 (usaf) government specification

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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